

# **NCE N-Channel Super Trench Power MOSFET**

### **Description**

The NCEP6055AGU uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

## **Application**

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

#### **General Features**

V<sub>DS</sub> =60V,I<sub>D</sub> =55A

 $R_{DS(ON)}$ =6.5m $\Omega$  (typical) @  $V_{GS}$ =10V  $R_{DS(ON)}$ =7.7m $\Omega$  (typical) @  $V_{GS}$ =4.5V

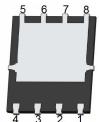
- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 150 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!

#### **DFN 5X6**

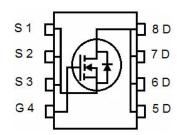


**Top View** 



4 3 2 1

Bottom View



**Schematic Diagram** 

#### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
P6055AGU	NCEP6055AGU	DFN5X6-8L	-	-	-

## Absolute Maximum Ratings (T<sub>C</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	60	V
Gate-Source Voltage	V <sub>G</sub> s	±20	V
Drain Current-Continuous	I <sub>D</sub>	55	Α
Drain Current-Continuous(T <sub>C</sub> =100 °C)	I <sub>D</sub> (100°C)	42.9	А
Pulsed Drain Current	I <sub>DM</sub>	220	А
Maximum Power Dissipation	P <sub>D</sub>	65	W
Derating factor		0.52	W/°C
Single pulse avalanche energy (Note 1)	E <sub>AS</sub>	350	mJ
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 150	$^{\circ}$ C



# NCEP6055AGU

#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case Resc 1.92 C/W	Thermal Resistance,Junction-to-Case	R <sub>eJC</sub>	1.92	°C/W
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#### Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·					
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	60		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics						•
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1.2	1.8	2.4	V
D : 0	-	V <sub>GS</sub> =10V, I <sub>D</sub> =25A	-	6.5	7.5	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =25A	-	7.7	8.8	
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =25A		60	-	S
Dynamic Characteristics	,					
Input Capacitance	C <sub>lss</sub>		-	2000	-	PF
Output Capacitance	Coss	$V_{DS}=30V, V_{GS}=0V,$	-	315	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	9.9	-	PF
Switching Characteristics (Note 2)	,					
Turn-on Delay Time	t <sub>d(on)</sub>		-	8	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =30 $V$ , $I_D$ =25 $A$	-	2	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}\text{=}10V, R_{G}\text{=}1.6\Omega$	-	29	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	4	-	nS
Total Gate Charge	Qg	.,	-	34.8	-	nC
Gate-Source Charge	Qgs	$V_{DS}$ =30 $V$ , $I_{D}$ =25 $A$ ,	-	7		nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	5.3		nC
Drain-Source Diode Characteristics					'	
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =25A	-		1.2	V
Diode Forward Current	Is		-	-	55	Α
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> =25A	-	38	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs	-	48	-	nC

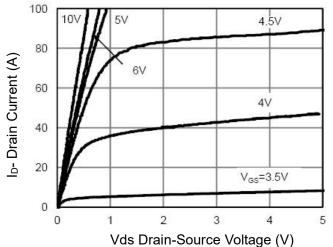
#### Notes:

<sup>1.</sup> EAS condition : Tj=25  $^{\circ}\text{C}\text{,V}_{\text{DD}}\text{=}30\text{V}\text{,V}_{\text{G}}\text{=}10\text{V}\text{,L=}0.5\text{mH}\text{,Rg=}25\Omega$ 

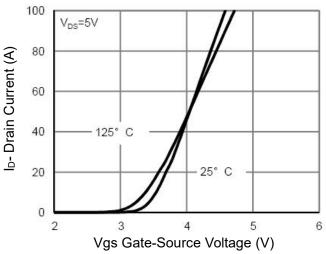
<sup>2.</sup> Guaranteed by design, not subject to production

<sup>3.</sup> These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsin k, assuming a maximum junction temperature of TJ(MAX)=150° C. The SOA curve provides a single pulse rating.

## **Typical Electrical and Thermal Characteristics**



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

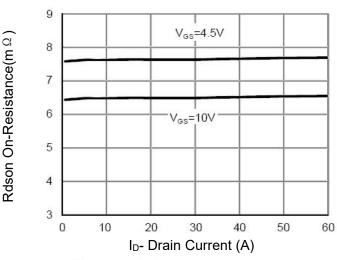
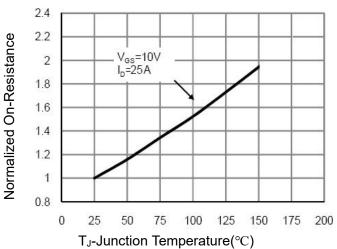


Figure 3 Rdson-Drain Current



**Figure 4 Rdson-Junction Temperature** 

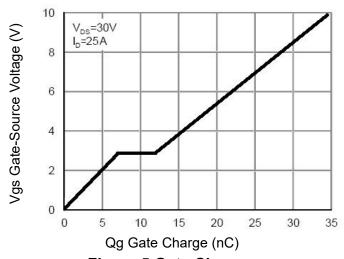


Figure 5 Gate Charge

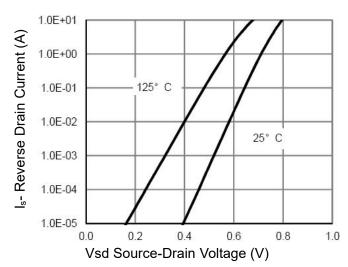


Figure 6 Source- Drain Diode Forward

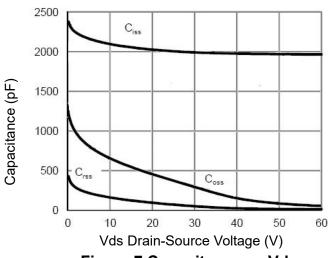


Figure 7 Capacitance vs Vds

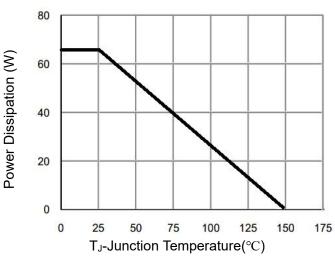


Figure 9 Power De-rating

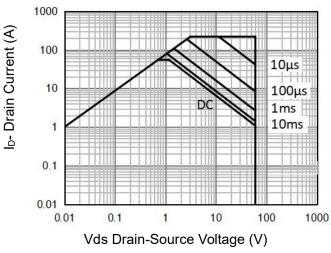


Figure 8 Safe Operation Area(Note 3)

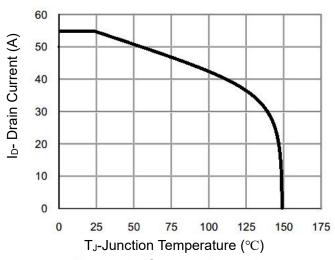


Figure 10 Current De-rating

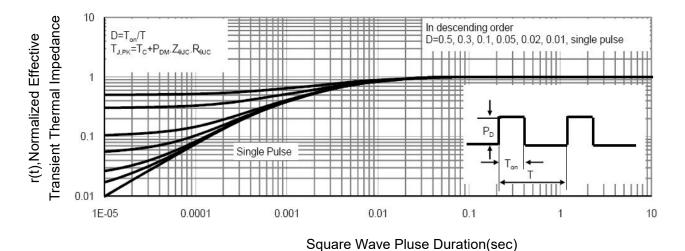
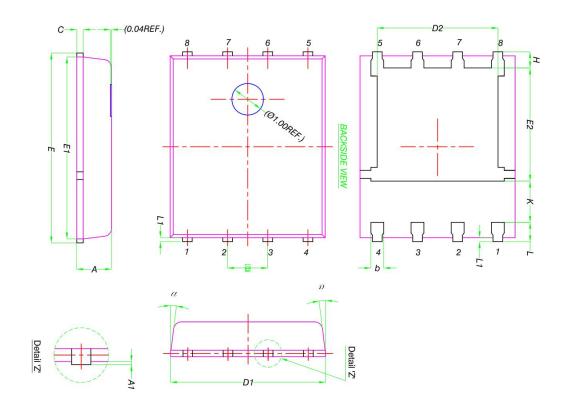
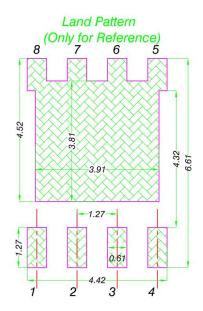


Figure 11 Normalized Maximum Transient Thermal Impedance

# DFN5X6-8L(G) Package Information



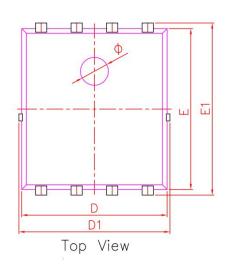
D/44	Λ	ILLIMETI	TERS		
DIM.	MIN.	NOM.	MAX.		
Α	0.90	1.00	1.10		
A1	0	8	0.05		
b	0.33	0.41	0.51		
С	0.20	0.25	0.30		
D1	4.80	4.90	5.00		
D2	3.61	3.81	3.96		
Ε	5.90	6.00	6.10		
E1	5.70	5.75	5.80		
E2	3.38	3.58	3.78		
е	1.27 BSC				
Н	0.41	0.51	0.61		
K	1.10	1-0	-		
L	0.51	0.61	0.71		
L1	0.06	0.13	0.20		
α	O°	121	12°		

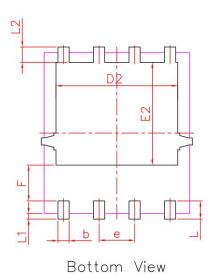


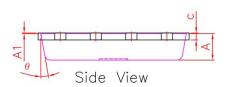
#### Note:

- 1. All Dimension Are In mm.
- Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs.
   Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
- 4. The Package Top May Be Smaller Than The Package Bottom.

# DFN5X6-8L(E) Package Information







	PDFN5X6-8L						
DIM.	MIN.	NOM.	MAX.				
Α	0.90	0.95	1.00				
A1	0.00	0.02	0.05				
b	0.35	0.40	0.50				
С	0.20	0.25	0.30				
D	5.10	5.20	5.30				
D1	5.10	5.40	5.50				
D2	4.25	4.35	4.45				
е	1.27 BSC						
Е	5.70	5.75	5.80				
E1	6.00	6.15	6.30				
E2	3.57	3.67	3.77				
F	1.18	1.28	1.38				
L	0.55	0.65	0.75				
L1	0.15	0.20	0.25				
L2	0.45	0.55	0.65				
Ø	0.90	1.00	1.10				
Θ	8°	10°	12°				
All dimensions in millimeters							

# NCEP6055AGU

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